

MCH3219-NPN Epitaxial Planar Silicon Transistor **DC / DC Converter Applications**

Applications

· Relay drivers, lamp drivers, motor drivers, flash.

Features

- · Adoption of MBIT processes.
- · Large current capacitance.
- · Low collector-to-emitter saturation voltage.
- · High-speed switching.
- Narrow hFE range.
- Ultrasmall package facilitates miniaturization in end products (mounting height : 0.85mm).
- · High allowable power dissipation.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		100	V
Collector-to-Emitter Voltage	VCES		100	V
	VCEO		50	V
Emitter-to-Base Voltage	VEBO		6	V
Collector Current	IC		1.0	А
Collector Current (Pulse)	ICP		3	А
Base Current	IB		200	mA
Collector Dissipation	PC	Mounted on a ceramic board (600mm ² X0.8m)	0.7	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Offic
Collector Cutoff Current	ICBO	V _{CB} =40V, I _E =0			0.1	μΑ
Emitter Cutoff Current	IEBO	VEB=4V, IC=0			0.1	μΑ
DC Current Gain	hFE	V _{CE} =2V, I _C =100mA	250		400	
Gain-Bandwidth Product	fT	V _{CE} =10V, I _C =300mA		420		MHz
Marking : CP Continued on next page						

Marking : CP

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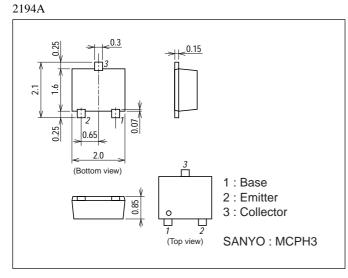
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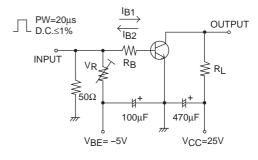
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Output Capacitance	Cob	VCB=10V, f=1MHz		6		pF
Collector-to-Emitter Saturation Voltage	V _{CE} (sat)	IC=500mA, IB=10mA		105	160	mV
Base-to-Emitter Saturation Voltage	VBE(sat)	IC=500mA, IB=10mA		0.81	1.2	V
Collector-to-Base Breakdown Voltage	V(BR)CBO	IC=10μA, IE=0	100			V
Collector-to-Emitter Breakdown Voltage	V(BR)CES	I _C =100μA, R _{BE} =0	100			V
	V(BR)CEO	IC=1mA, RBE=∞	50			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	I _E =10μA, I _C =0	6			V
Turn-ON Time	ton	See specified Test Circuit.		38		ns
Storage Time	tstg	See specified Test Circuit.		332		ns
Fall Time	tf	See specified Test Circuit.		40		ns

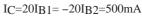
Package Dimensions

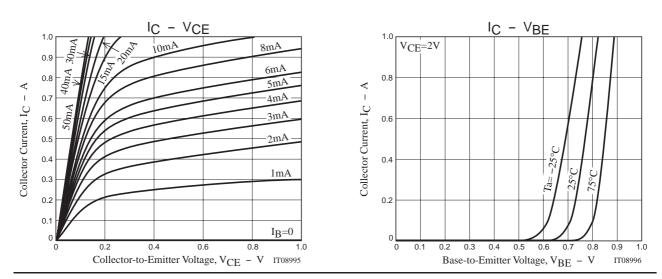
unit : mm

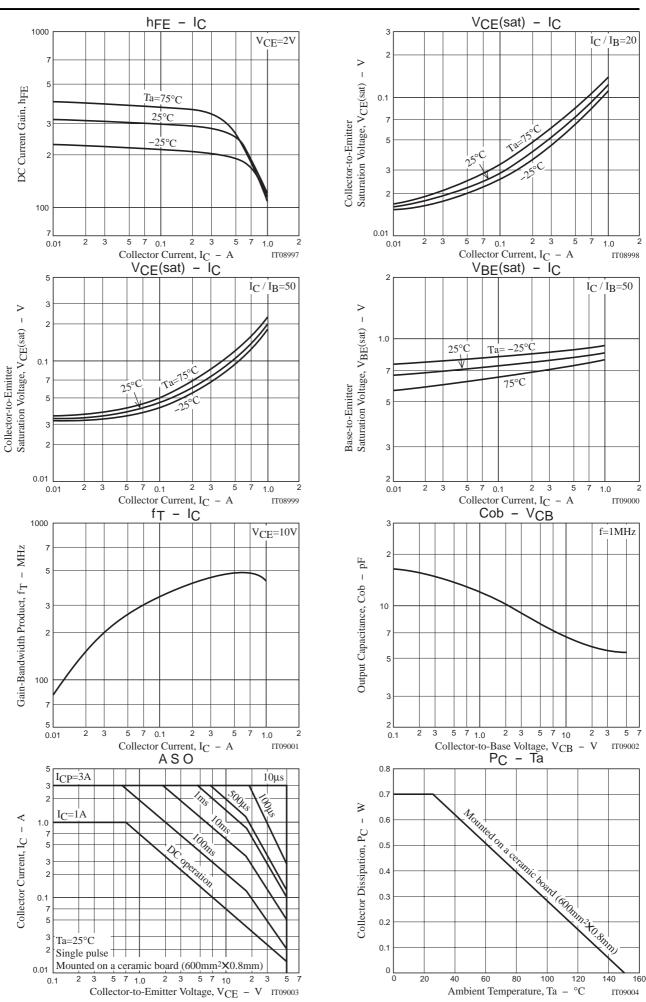


Switching Time Test Circuit









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